

## • Aim

- » To study the effect of the two strain models in NEMO3D on the atomic and electronic structure of pure InAs/ GaAs QD's.

## • Procedure

- » Set up device in NEMO3D
- » Set lattice constant of structure = lattice constant of GaAs.
- » Minimize total strain energy w.r.t each atomic position → find relaxed atomic positions ( $R_i$ )
- » Set up Tight Binding Hamiltonian using bulk params. and ( $R_i$ ) and solve Schrödinger equation
- » Repeat for anharmonic strain model.

## • Result

- » Both strain models → InAs is only compressively strained. (-1 to -5%)
- » Strain in Anharmonic model < Strain in harmonic model.

